

Abstract

Resonator and Preparation Method For a Resonator

The present application provides a resonator and a preparation method for a resonator, and relates to the technical field of semiconductors. The method involves introducing a first single crystal substrate to facilitate the epitaxial growth of a high-quality single crystal piezoelectric layer on the first single crystal substrate, and firstly performing ion implantation on the first single crystal substrate to form a damaged layer at a certain depth within it. Therefore, while the first single crystal substrate is removed, it is firstly possible to adopt the heating process, and after the first single crystal substrate is subjected to high-temperature treatment, a first layer and a second layer are split at the damaged layer, thereby a part of the first single crystal substrate is firstly removed, and then the remaining part of the first single crystal substrate is removed by trimming, etching, and other modes. By cooperation of two removing modes, the rapid removal of the first single crystal substrate is achieved, and the difficulty of removing the first single crystal substrate is effectively reduced.

Figure 1